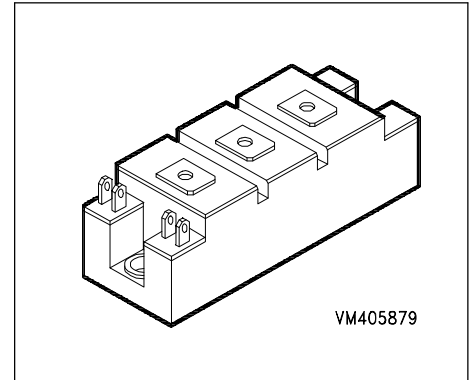


IGBT Power Module

- Half-bridge
- Including fast free-wheeling diodes
- Package with insulated metal base plate
- $R_{G\ on,min} = 22\ \Omega$



Type	V_{CE}	I_C	Package	Ordering Code
BSM 75 GB 170 DN2	1700V	110A	HALF-BRIDGE 1	C67070-A2702-A67

Maximum Ratings

Parameter	Symbol	Values	Unit
Collector-emitter voltage	V_{CE}	1700	V
Collector-gate voltage	V_{CGR}		
$R_{GE} = 20\text{ k}\Omega$		1700	
Gate-emitter voltage	V_{GE}	± 20	
DC collector current	I_C		A
$T_C = 25\text{ }^{\circ}\text{C}$		110	
$T_C = 80\text{ }^{\circ}\text{C}$		75	
Pulsed collector current, $t_p = 1\text{ ms}$	I_{Cpuls}		
$T_C = 25\text{ }^{\circ}\text{C}$		220	
$T_C = 80\text{ }^{\circ}\text{C}$		150	
Power dissipation per IGBT	P_{tot}		W
$T_C = 25\text{ }^{\circ}\text{C}$		625	
Chip temperature	T_j	+ 150	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-40 ... + 125	
Thermal resistance, chip case	R_{thJC}	≤ 0.2	K/W
Diode thermal resistance, chip case	R_{thJCD}	≤ 0.63	
Insulation test voltage, $t = 1\text{min.}$	V_{is}	4000	Vac
Creepage distance	-	16	mm
Clearance	-	11	
DIN humidity category, DIN 40 040	-	F	sec
IEC climatic category, DIN IEC 68-1	-	40 / 125 / 56	

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Static Characteristics

Gate threshold voltage $V_{GE} = V_{CE}, I_C = 5\text{ mA}$	$V_{GE(th)}$	4.8	5.5	6.2	V
Collector-emitter saturation voltage $V_{GE} = 15\text{ V}, I_C = 75\text{ A}, T_j = 25\text{ °C}$ $V_{GE} = 15\text{ V}, I_C = 75\text{ A}, T_j = 125\text{ °C}$	$V_{CE(sat)}$	- -	3.4 4.6	3.9 5.3	
Zero gate voltage collector current $V_{CE} = 1700\text{ V}, V_{GE} = 0\text{ V}, T_j = 25\text{ °C}$ $V_{CE} = 1700\text{ V}, V_{GE} = 0\text{ V}, T_j = 125\text{ °C}$	I_{CES}	- -	0.5 2	0.75 -	
Gate-emitter leakage current $V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$	I_{GES}	-	-	400	nA

AC Characteristics

Transconductance $V_{CE} = 20\text{ V}, I_C = 75\text{ A}$	g_{fs}	27	-	-	S
Input capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{iss}	-	11	-	nF
Output capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{oss}	-	1	-	
Reverse transfer capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{rss}	-	0.28	-	

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Switching Characteristics, Inductive Load at $T_j = 125\text{ °C}$

Turn-on delay time $V_{CC} = 1200\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 75\text{ A}$ $R_{Gon} = 22\text{ }\Omega$	$t_{d(on)}$	-	400	800	ns
Rise time $V_{CC} = 1200\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 75\text{ A}$ $R_{Gon} = 22\text{ }\Omega$	t_r	-	150	300	
Turn-off delay time $V_{CC} = 1200\text{ V}$, $V_{GE} = -15\text{ V}$, $I_C = 75\text{ A}$ $R_{Goff} = 22\text{ }\Omega$	$t_{d(off)}$	-	650	1000	
Fall time $V_{CC} = 1200\text{ V}$, $V_{GE} = -15\text{ V}$, $I_C = 75\text{ A}$ $R_{Goff} = 22\text{ }\Omega$	t_f	-	90	140	

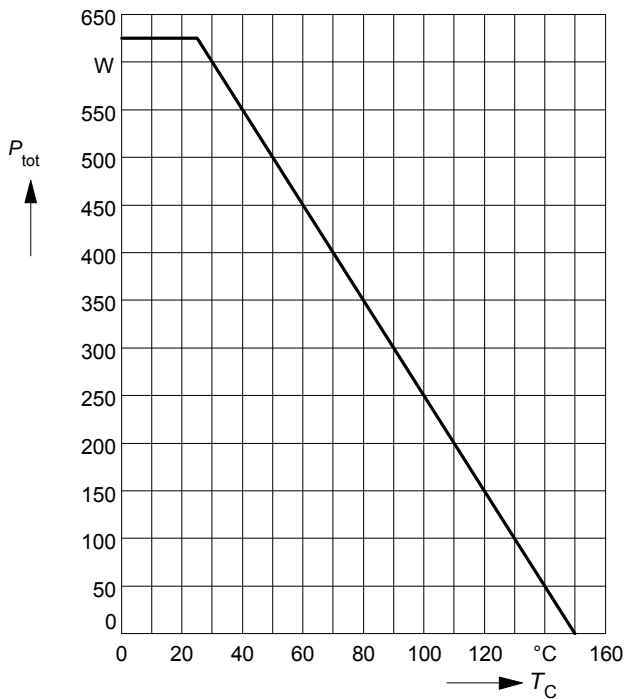
Free-Wheel Diode

Diode forward voltage $I_F = 75\text{ A}$, $V_{GE} = 0\text{ V}$, $T_j = 25\text{ °C}$ $I_F = 75\text{ A}$, $V_{GE} = 0\text{ V}$, $T_j = 125\text{ °C}$	V_F	-	2.3 2.1	2.8 -	V
Reverse recovery time $I_F = 75\text{ A}$, $V_R = -1200\text{ V}$, $V_{GE} = 0\text{ V}$ $di_F/dt = -800\text{ A}/\mu\text{s}$, $T_j = 125\text{ °C}$	t_{rr}	-	0.3	-	
Reverse recovery charge $I_F = 75\text{ A}$, $V_R = -1200\text{ V}$, $V_{GE} = 0\text{ V}$ $di_F/dt = -800\text{ A}/\mu\text{s}$ $T_j = 25\text{ °C}$ $T_j = 125\text{ °C}$	Q_{rr}	-	7 21	- -	μC
		-			

Power dissipation

$$P_{\text{tot}} = f(T_C)$$

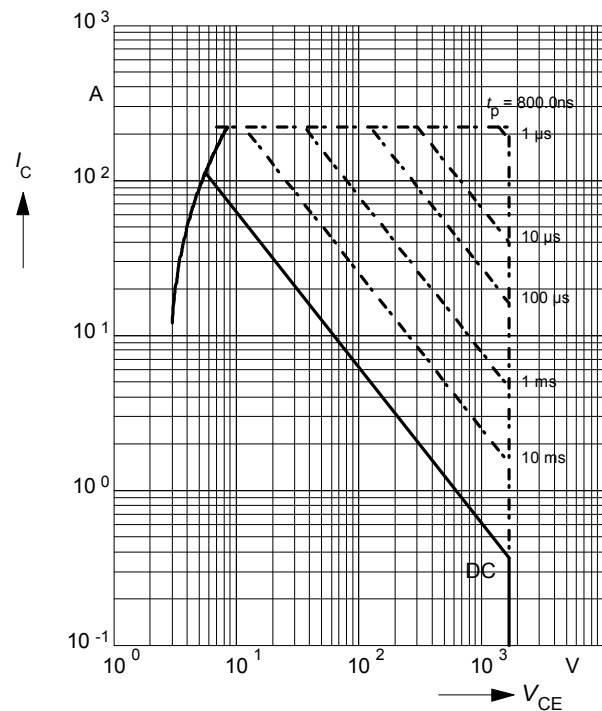
parameter: $T_j \leq 150^\circ\text{C}$



Safe operating area

$$I_C = f(V_{CE})$$

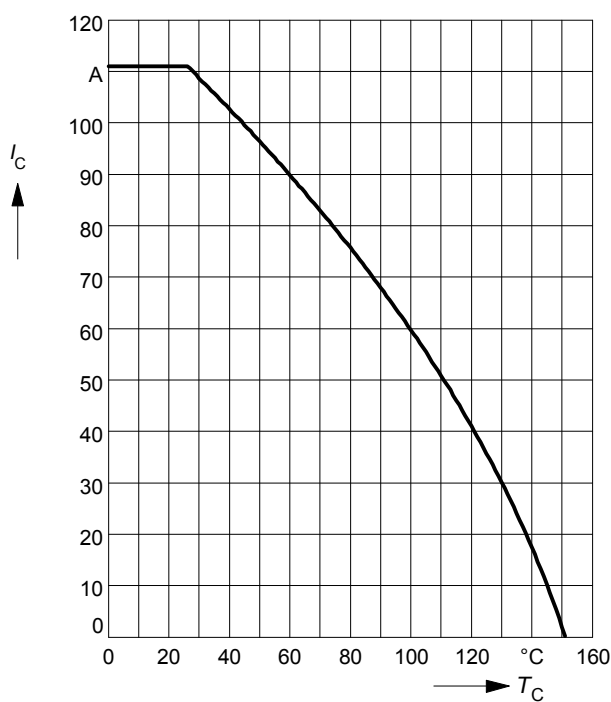
parameter: $D = 0$, $T_C = 25^\circ\text{C}$, $T_j \leq 150^\circ\text{C}$



Collector current

$$I_C = f(T_C)$$

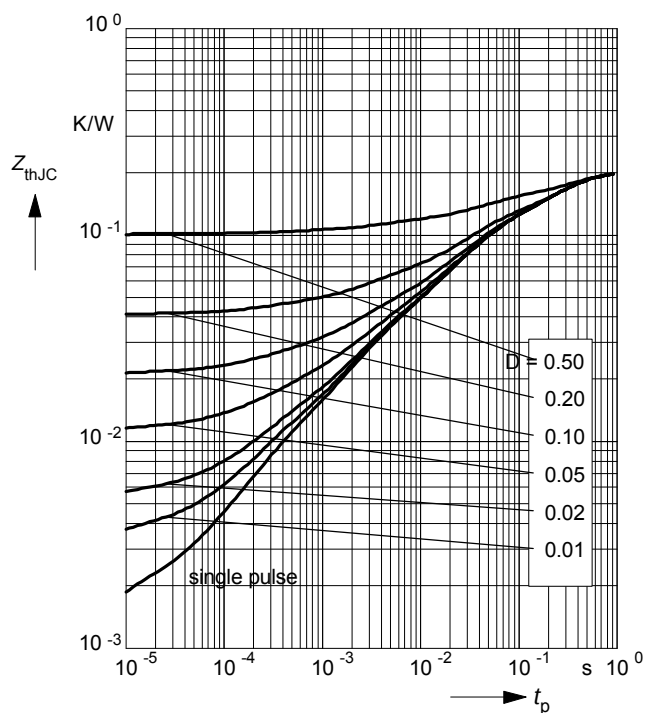
parameter: $V_{GE} \geq 15\text{ V}$, $T_j \leq 150^\circ\text{C}$



Transient thermal impedance IGBT

$$Z_{\text{thJC}} = f(t_p)$$

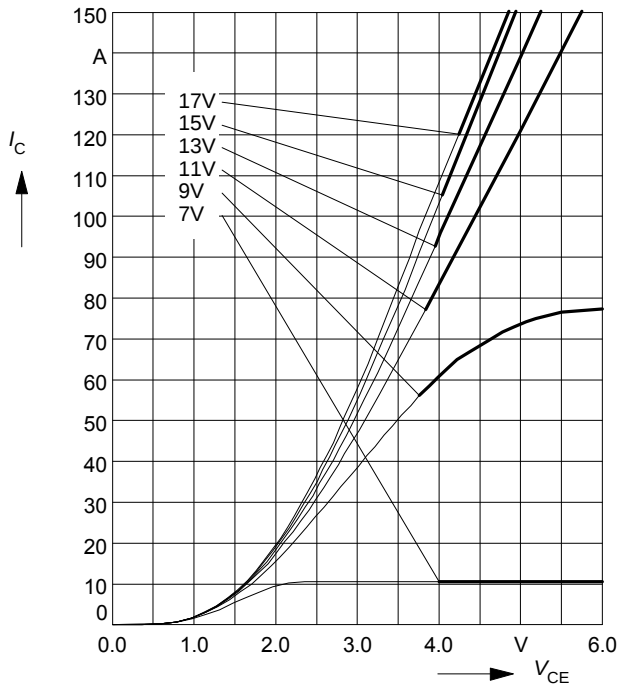
parameter: $D = t_p / T$



Typ. output characteristics

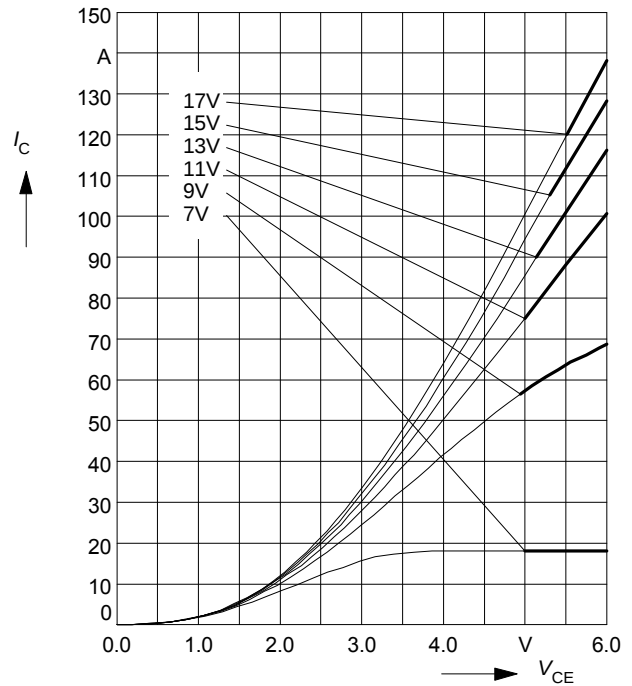
$$I_C = f(V_{CE})$$

parameter: $t_p = 80 \mu s$, $T_j = 25^\circ C$

**Typ. output characteristics**

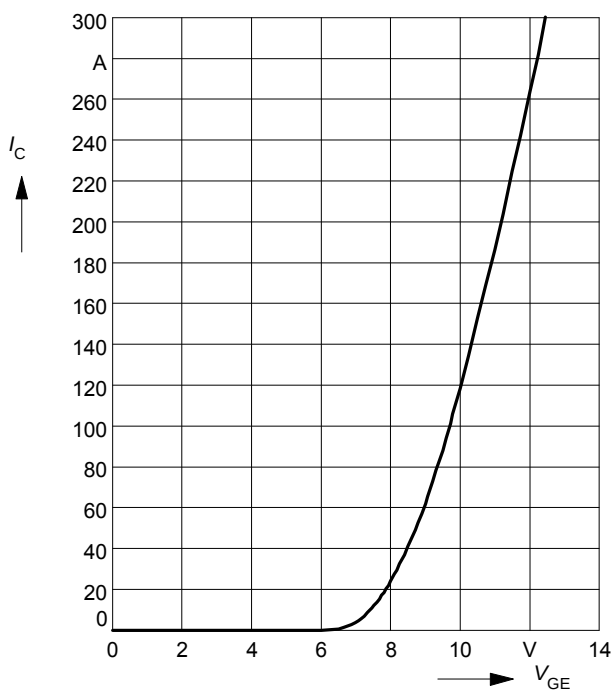
$$I_C = f(V_{CE})$$

parameter: $t_p = 80 \mu s$, $T_j = 125^\circ C$

**Typ. transfer characteristics**

$$I_C = f(V_{GE})$$

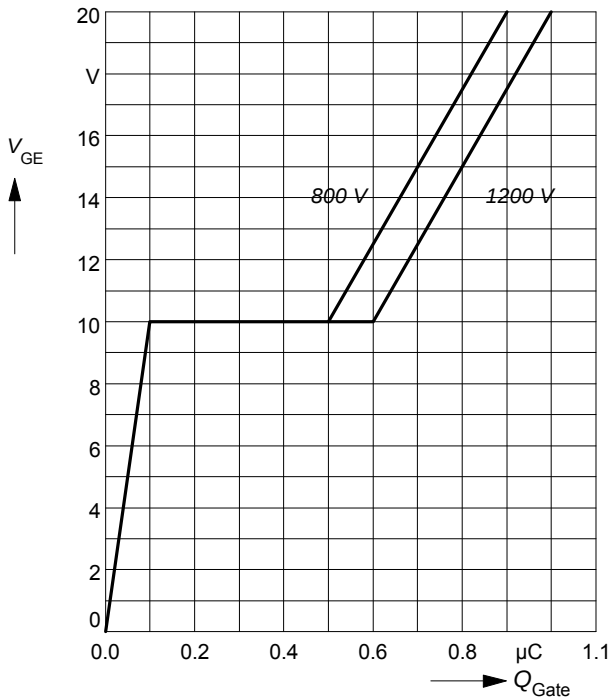
parameter: $t_p = 80 \mu s$, $V_{CE} = 20 V$



Typ. gate charge

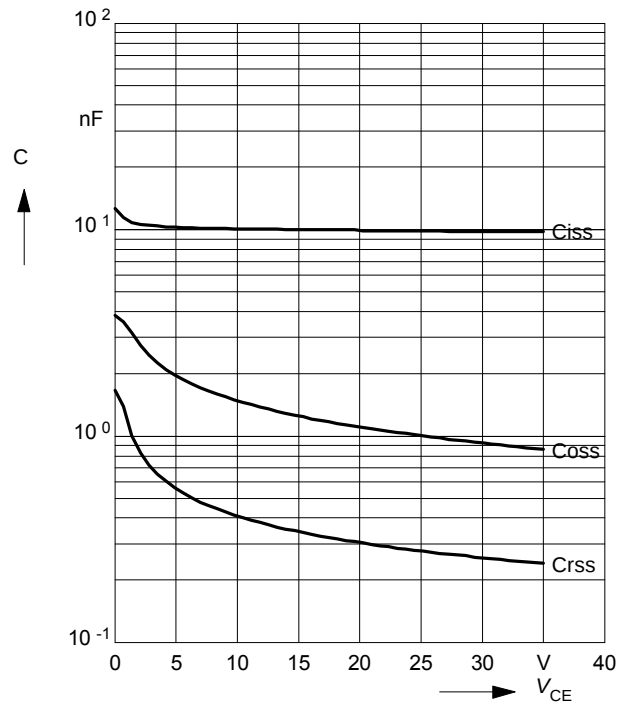
$$V_{GE} = f(Q_{Gate})$$

parameter: $I_{C\ puls} = 75\ A$

**Typ. capacitances**

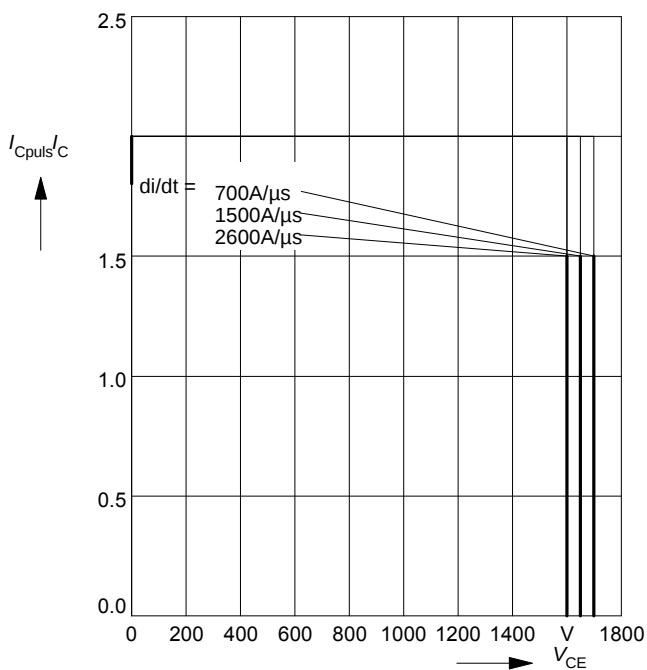
$$C = f(V_{CE})$$

parameter: $V_{GE} = 0$, $f = 1\ MHz$

**Reverse biased safe operating area**

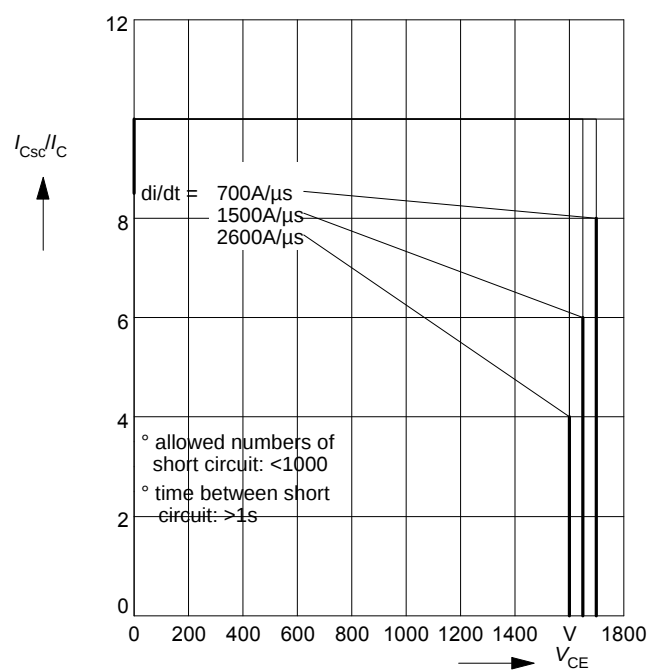
$$I_{C\ puls} = f(V_{CE}), T_j = 150^\circ C$$

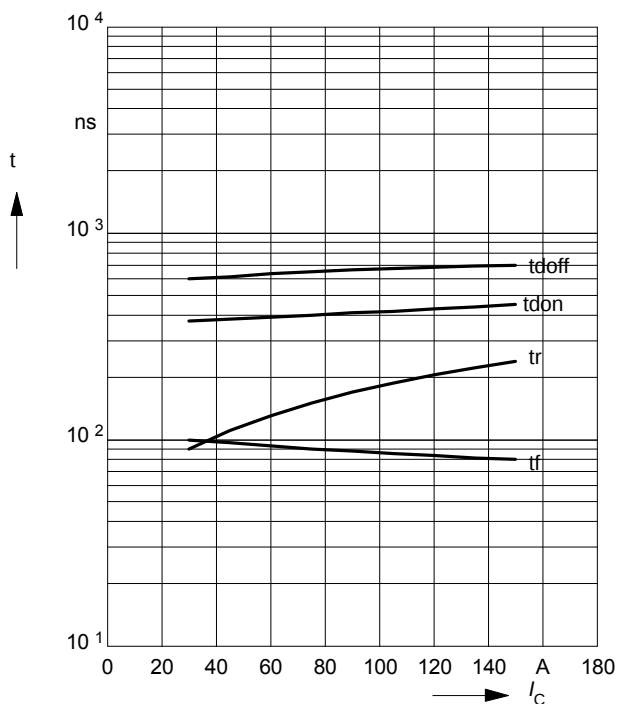
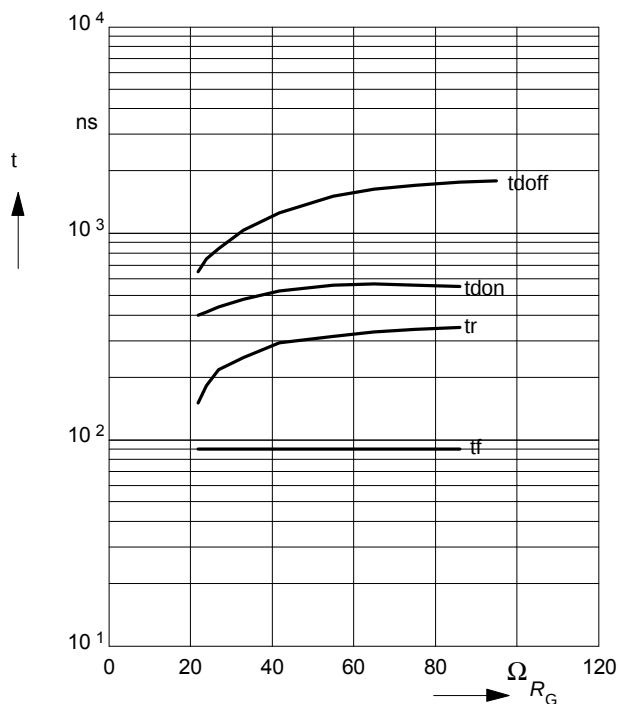
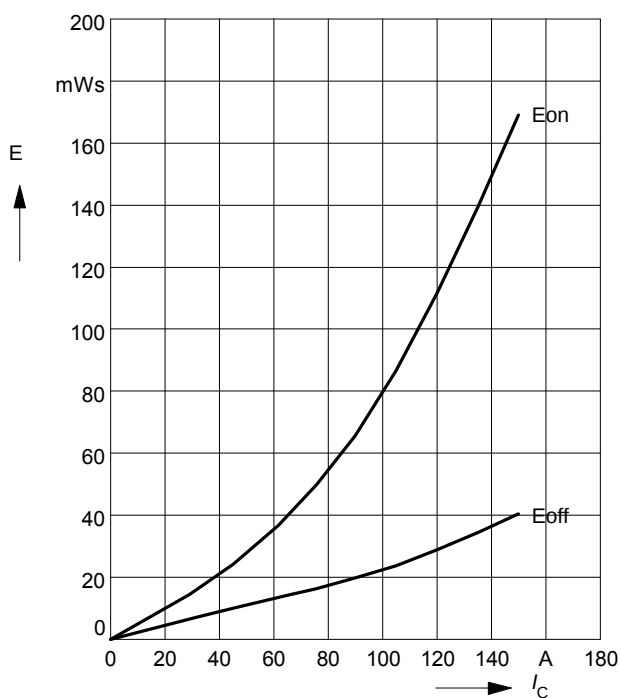
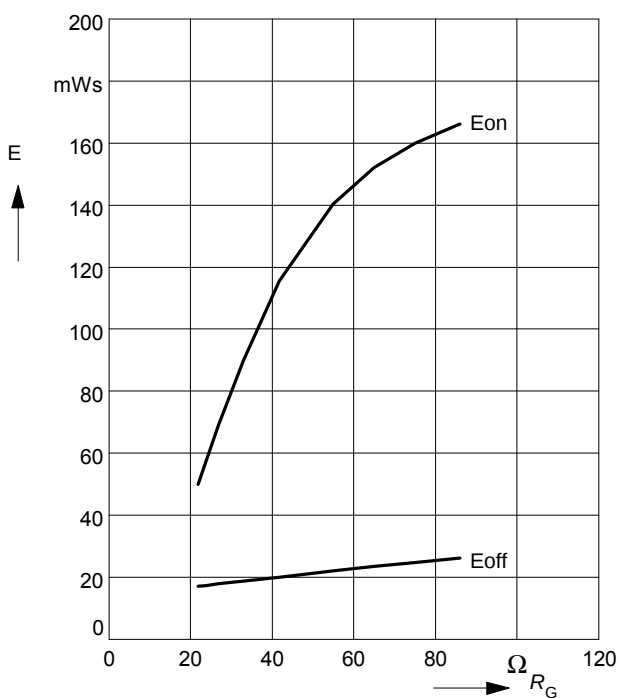
parameter: $V_{GE} = \pm 15\ V$, $t_p \leq 1\ ms$, $L < 50\ nH$

**Short circuit safe operating area**

$$I_{C\ sc} = f(V_{CE}), T_j = 150^\circ C$$

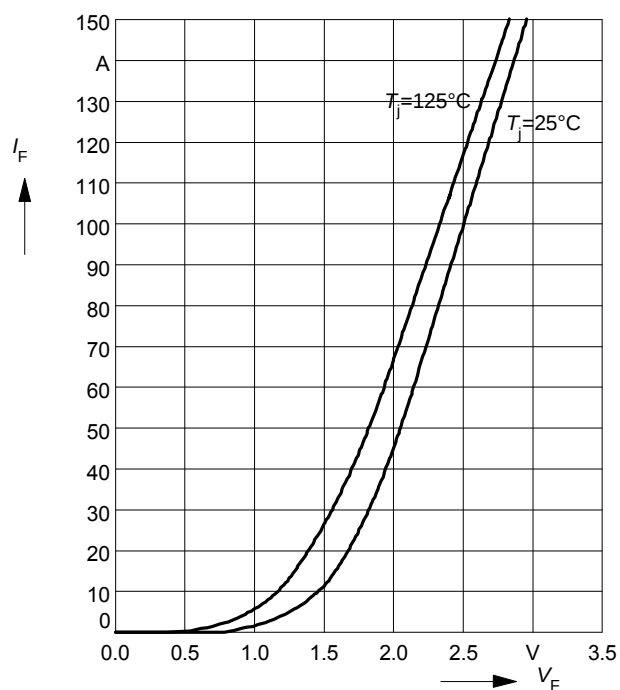
parameter: $V_{GE} = \pm 15\ V$, $t_p \leq 10\ \mu s$, $L < 50\ nH$



Typ. switching time $I = f(I_C)$, inductive load, $T_j = 125^\circ\text{C}$ par.: $V_{CE} = 1200\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $R_G = 22\ \Omega$ **Typ. switching time** $t = f(R_G)$, inductive load, $T_j = 125^\circ\text{C}$ par.: $V_{CE} = 1200\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $I_C = 75\text{ A}$ **Typ. switching losses** $E = f(I_C)$, inductive load, $T_j = 125^\circ\text{C}$ par.: $V_{CE} = 1200\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $R_G = 22\ \Omega$ **Typ. switching losses** $E = f(R_G)$, inductive load, $T_j = 125^\circ\text{C}$ par.: $V_{CE} = 1200\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $I_C = 75\text{ A}$ 

Forward characteristics of fast recovery reverse diode $I_F = f(V_F)$

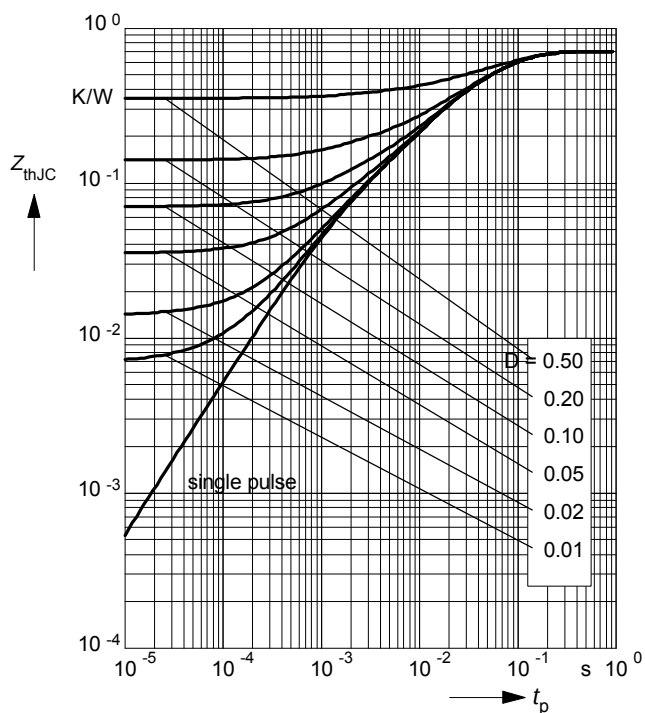
parameter: T_j

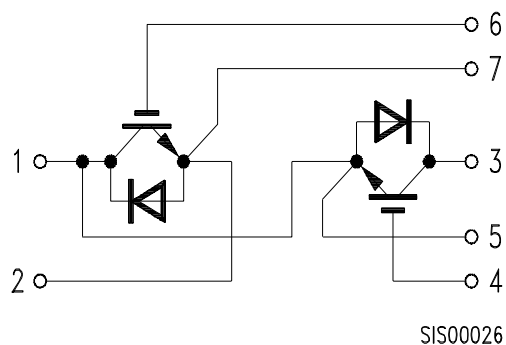


Transient thermal impedance Diode

$$Z_{thJC} = f(t_p)$$

parameter: $D = t_p / T$



Circuit Diagram**Package Outlines**

Dimensions in mm

Weight: 250 g

